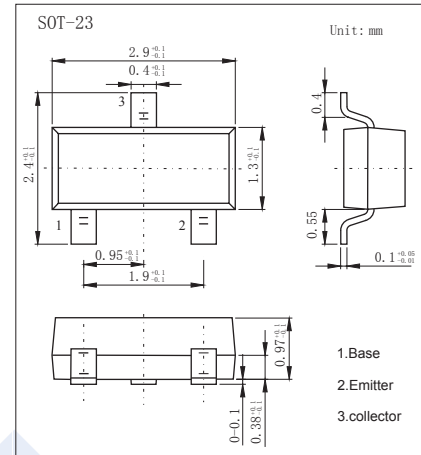


NPN Transistors

2SC4366

■ Features

- Collector Current Capability $I_c=300\text{mA}$
- Collector Emitter Voltage $V_{CE0}=50\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	60	V
Collector - Emitter Voltage	V_{CE0}	50	
Emitter - Base Voltage	V_{EB0}	15	
Collector Current - Continuous	I_c	300	mA
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}$, $I_E = 0$	60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{mA}$, $I_B = 0$	50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}$, $I_C = 0$	15			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 50 \text{V}$, $I_E = 0$			1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 15\text{V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 300\text{mA}$, $I_B = 30\text{mA}$			0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 300\text{mA}$, $I_B = 30\text{mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$			0.75	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_c = 100\text{mA}$	800		2000	
		$V_{CE} = 6\text{V}$, $I_c = 1\text{mA}$	500			

■ Marking

Marking	ZI*
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■ Typical Characteristics

